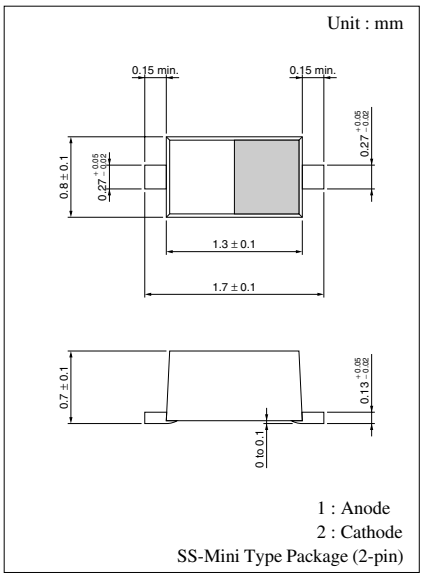
MA2S331

Silicon epitaxial planar type

For VCO of an UHF radio



Marking Symbol: F

■ Features

- Small series resistance $r_{D.}$ r_D = 0.18 Ω (typ.)
- Good linearity of C – V curve
- SS-mini package, optimum for down-sizing of equipment

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	12	V
Forward current (DC)	I_F	20	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

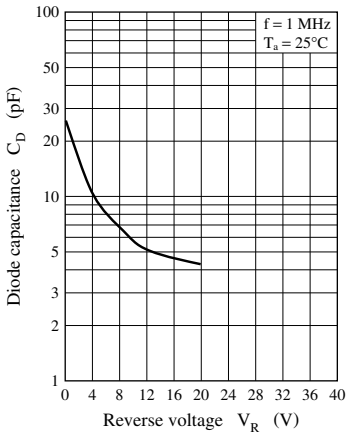
■ Electrical Characteristics T_a = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	V_R = 12 V			10	nA
Diode capacitance	$C_{D(1V)}$	V_R = 1 V, f = 1 MHz	17.0		20.0	pF
	$C_{D(2V)}$	V_R = 2 V, f = 1 MHz	14.0	15.0	16.0	pF
	$C_{D(4V)}$	V_R = 4 V, f = 1 MHz	10.0		12.4	pF
	$C_{D(10V)}$	V_R = 10 V, f = 1 MHz	5.5	6.0	6.5	pF
Capacitance ratio	$C_{D(1V)}/C_{D(4V)}$		1.53	1.6	1.83	—
	$C_{D(2V)}/C_{D(10V)}$		2.25	2.5	2.75	—
Series resistance*	r_D	C_D = 9 pF, f = 470 MHz		0.18	0.22	Ω

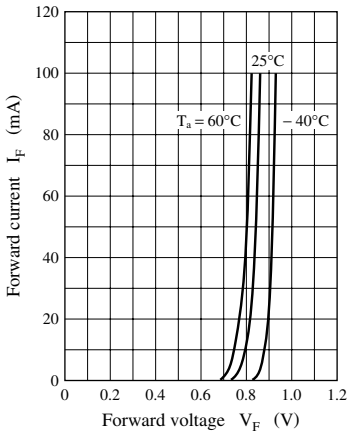
Note) 1. Rated input/output frequency: 470 MHz

2. * : r_f measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

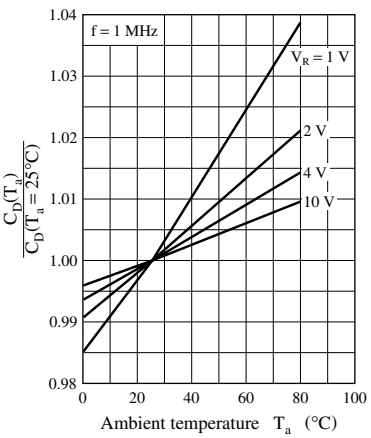
C_D — V_R



I_F — V_F



C_D — T_a



I_R — T_a